





Phase Control Thyristor

DS6077-2 August 2016 (LN33766)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR2450W85* DCR2450W80 DCR2450W75 DCR2450W70	8500 8000 7500 7000	$\begin{split} T_{vj} = -40^{\circ} & \text{C to } 125^{\circ} \text{ C,} \\ I_{DRM} = I_{RRM} = 300\text{mA,} \\ V_{DRM}, & V_{RRM} & t_p = 10\text{ms,} \\ V_{DSM} & & V_{RSM} = \\ V_{DRM} & & V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. * 8200V @ -40° C, 6500V @ 0° C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR2450W85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	8500V
$I_{T(AV)}$	2450A
I _{TSM}	35200A
dV/dt*	1500V/µs
dl/dt	300A/μs

* Higher dV/dt selections available

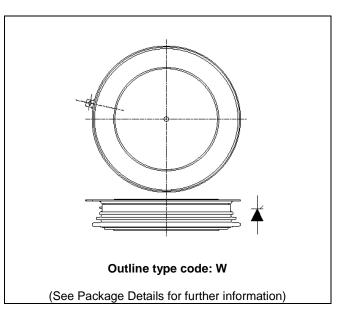


Fig. 1 Package outline





CURRENT RATINGS

T_{case} = 60° C unless stated otherwise

Symbol	Symbol Parameter Test Conditions		Max.	Units
Double Sid	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load		А
I _{T(RMS)}	RMS value	-		А
Ι _Τ	Continuous (direct) on-state current	-	3750	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125° C	35.2	kA
l ² t	I ² t for fusing	$V_R = 0$	6.2	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	Min.	Max.	Units	
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	Double side cooled DC		0.00631	° C/W
		Single side cooled Anode DC		-	0.01115	° C/W
			Cathode DC	-	0.01453	° C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 76.0kN Double side		-	0.0014	° C/W
		(with mounting compound)	Single side	-	0.0028	° C/W
T _{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
Fm	Clamping force			68.0	84.0	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	Test Conditions		Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125° C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}$ C, g	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	150	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	300	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ} C$				
V _{T(TO)}	Threshold voltage – Low level	500 to 2400A at T _{case} = 125°	С	-	1.037	V
	Threshold voltage – High level	2400 to 7200A at T _{case} = 125° C		-	1.229	V
r _T	On-state slope resistance – Low level	500A to 2400A at T _{case} = 125° C		-	0.487	mΩ
	On-state slope resistance – High level	2400A to 7200A at T _{case} = 125° C		-	0.398	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10Ω		-	3	μs
		$t_r = 0.5 \mu s$, $T_j = 25^{\circ} C$				
tq	Turn-off time	$T_j = 125^{\circ} \text{ C}, V_R = 200 \text{V}, \text{ dI/dt}$	= 1A/µs,	-	1000	μs
		dV _{DR} /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 2000A$, $T_j = 125^{\circ}$ C, $dI/dt - 1A/\mu s$,		2800	9000	μC
IL	Latching current	$T_j = 25^{\circ} \text{ C}, V_D = 5V$		-	3	Α
IH	Holding current	$T_j = 25^{\circ} \text{ C}, R_{G-K} = \infty, I_{TM} = 50$	00A, I _T = 5A	-	300	mA





GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25° C	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25° C	400	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

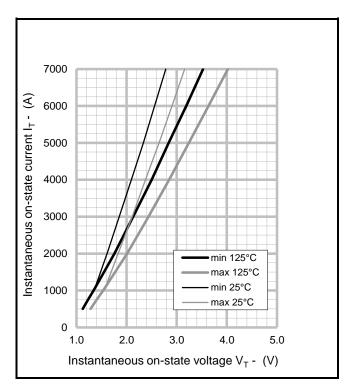


Fig.2 Maximum & minimum on-state characteristics

 V_{TM} EQUATION

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$

where A = 0.907134

B = -0.011004

C = 0.000304

D = 0.012936

these values are valid for T_j = 125°C for I_T 500A to 7200A



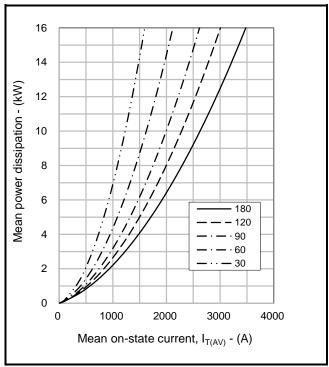


Fig.3 On-state power dissipation - sine wave

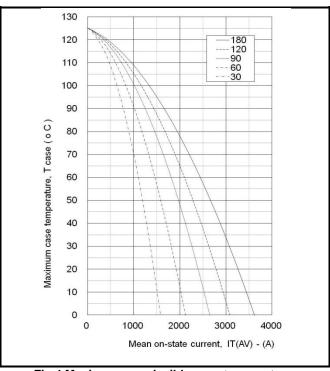


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

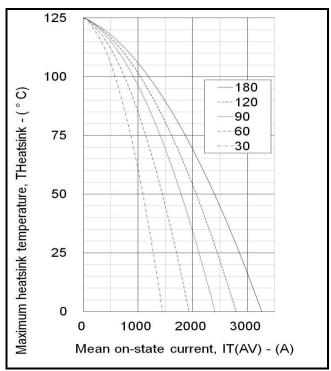


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

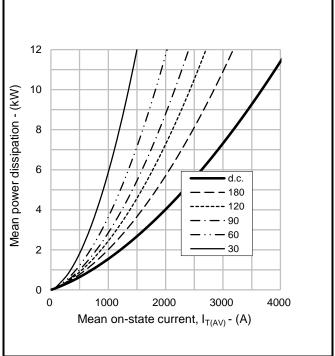


Fig.6 On-state power dissipation - rectangular wave

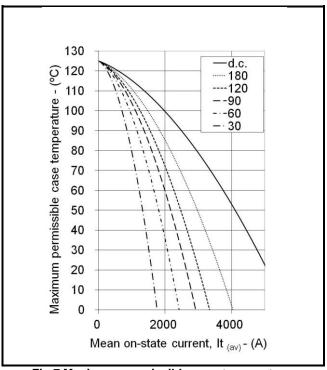


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

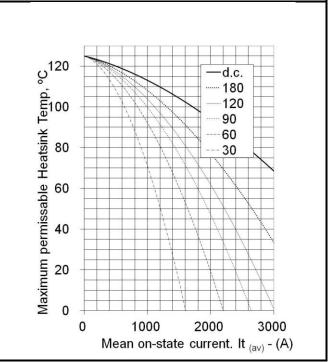
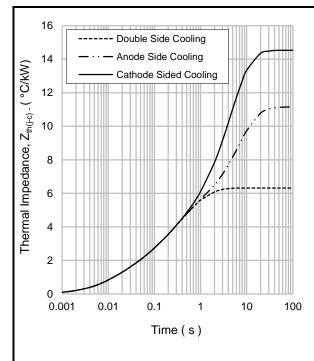


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R _i (°C/kW)	0.8816	1.2993	2.8048	1.3305
	T _i (s)	0.0106818	0.058404	0.3584979	1.1285
Anode side cooled	R _i (°C/kW)	1.5197	3.2398	5.7622	0.6312
	T _i (s)	0.0170581	0.2424644	6.013	15.364
Cathode side cooled	R _i (°C/kW)	1.4106	2.4667	6.7451	3.9054
	T _i (s)	0.0158344	0.1786951	3.6201	6.196

 $Z_{th} = \sum [R_i x (1-exp. (t/t_i))]$ [1]

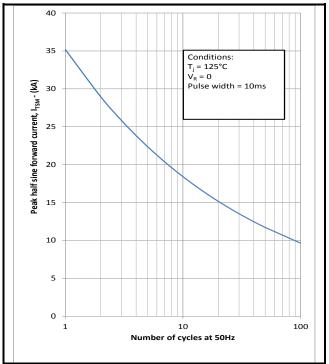
 $\Delta R_{th(j-c)}$ Conduction

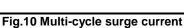
Tables show the increments of thermal resistance $R_{\text{th(j-c)}}$ when the device operates at conduction angles other than d.c.

Double side cooling			Anode Side Cooling			
	ΔZ_{th} (z)			ΔZ_{th} (z)		
θ°	sine.	rect.	θ°	sine.	rect.	
180	1.00	0.67	180	0.94	0.64	
120	1.16	0.97	120	1.08	0.91	
90	1.33	1.13	90	1.23	1.06	
60	1.48	1.31	60	1.37	1.22	
30	1.61	1.51	30	1.47	1.38	
4.5	4.00	4.04	4.5	4.50	4 47	

Cathode Sided Cooling					
	$\Delta Z_{th}(z)$				
θ°	sine. rect.				
180	0.95	0.65			
120	1.09	0.92			
90	1.25	1.07			
60	1.38	1.23			
30	1.49	1.40			

Fig.9 Maximum (limit) transient thermal impedance - junction to case (° C/kW)





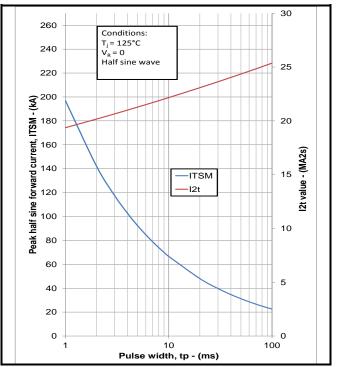


Fig.11 Single-cycle surge current

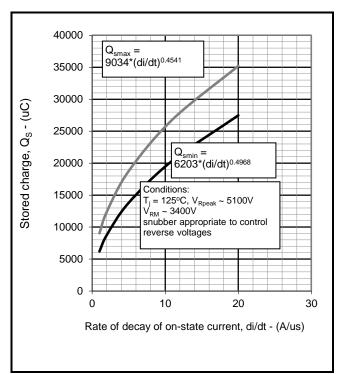


Fig.10 Reverse recovery charge

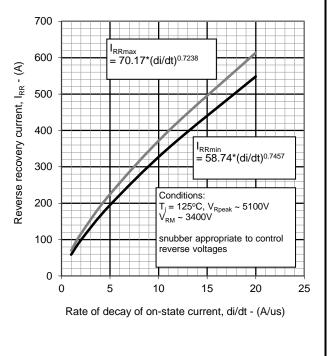


Fig.11 Reverse recovery current

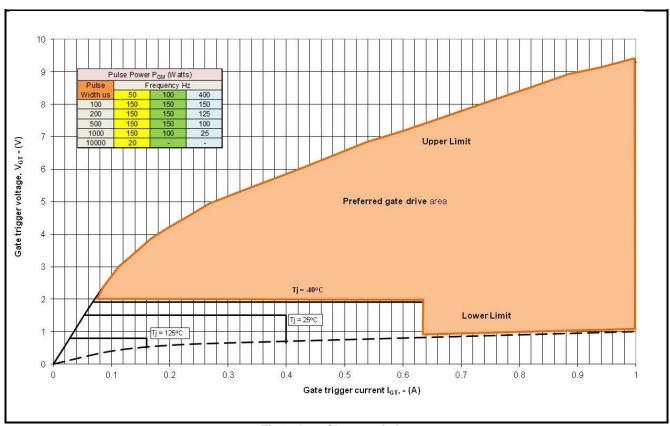


Fig12 Gate Characteristics

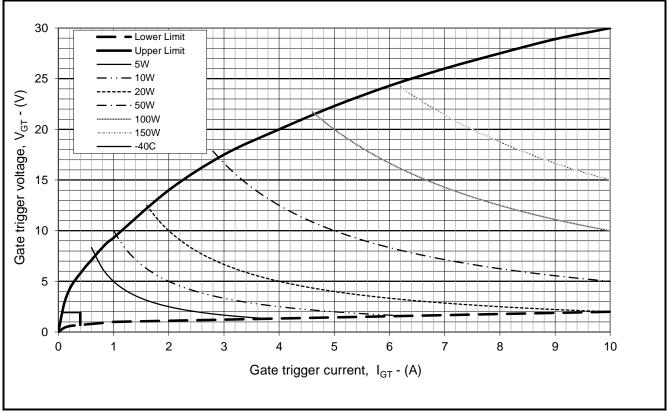


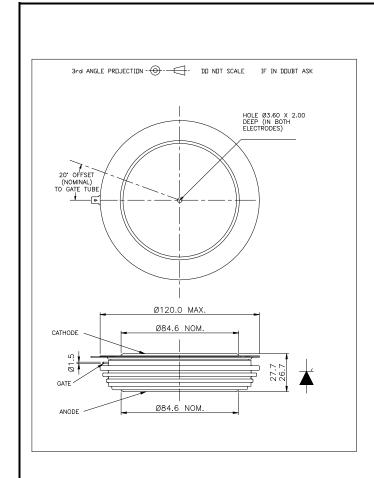
Fig. 13 Gate characteristics





PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



		Minimu
	Maximum	m
	Thickness	Thickne
Device	(mm)	ss (mm)
DCR2450W85	28.31	27.76
DCR2950W65	27.95	27.4
DCR3640W52	27.69	27.14
DCR4100W42	27.57	27.02
DCR4910W28	27.34	26.79

Clamping force: 76kN ±10% Lead length: 420mm Lead terminal connector: M4 ring Weight: 1.55kg Package outline type code: W

Fig.14 Package outline





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HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LIMITED Doddington Road, Lincoln, Lincolnshire, LN6 3LF

United Kingdom.

No Annotation:

Phone: +44 (0) 1522 500500 Fax: +44 (0) 1522 500550 Web: http://www.dynexsemi.com

CUSTOMER SERVICE

Phone: +44 (0) 1522 502753 / 502901

Fax: +44 (0) 1522 500020

e-mail: power_solutions@dynexsemi.com

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